

# **Parasitic Extraction Involving 3-D Conductors Based on Multi- layered Green's Function**

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# Abstract

- ◆ An algorithm for capacitance extraction based on Green's function involving 3-D conductors, considering multi-layered dielectric and lossy substrate
- ◆ An Improvement based on an algorithm implemented in ASITIC, for which the metal thickness cannot be included.
- ◆ A numerically stable and analytically integrable formula for the Green's function in vertical direction is derived
- ◆ The Green's function is integrated over the sidewalls
- ◆ The coefficient of potential is efficiently calculated by looking up the table of DCT, DCST and DST

# Outline

- ◆ Background
- ◆ DCT based Green's function method
- ◆ Our algorithm
- ◆ Result and Comparison
- ◆ Conclusion

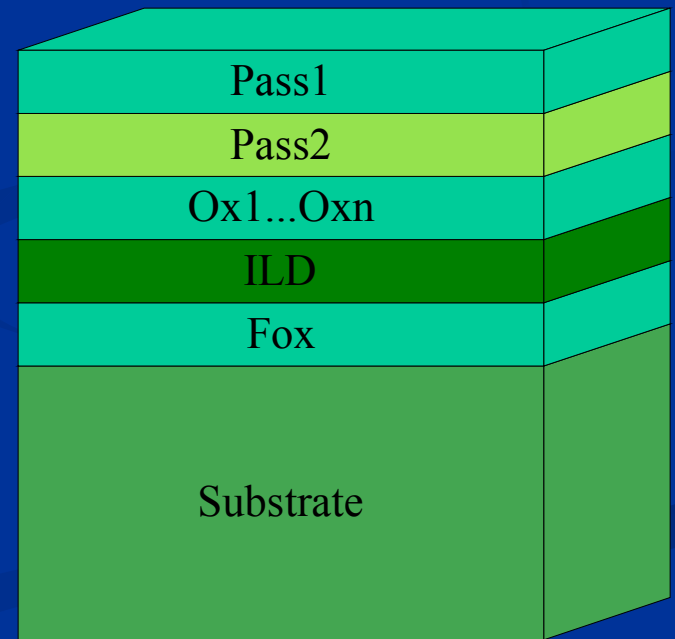
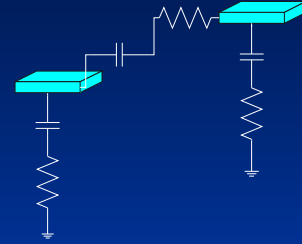
# Capacitive Parasitic Extraction Based on BEM

$$Pq = v$$

- ◆ Computing the coefficient-of-potential  $p_{ij}$ 
    - Free space method (Direct BEM)
    - Green's function method
  - ◆ Solving the equation  $Pq=v$ 
    - LU decomposition
    - Fast Multi-pole Method (J. White, MIT)
    - Singular Value Decomposition (S. Kapur, Bell Lab)
    - Hierarchical Method (W. Shi, TAMU)
    - Quasi Multiple Media (W. Yu, THU)
    - ...
- } kernel independent

# Advantages of Green's Function Method

- ◆ Direct BEM method
  - Discretize the interfaces between each adjacent dielectrics
  - A Large number of variables
- ◆ Green's function method
  - Layout independent Green's function for technology is solved first
  - Dielectric information is included in the Green's function
  - Only conductors need to be discretized
  - Limited to some certain profiles.



# DCT Based Green's Function Method

- ◆ Based on multi-layered Green's function
- ◆ First proposed by R. Gharpurey in 1996 to analyze the effect of substrate coupling
- ◆ Numerically stabilized by A.M. Niknejad in 1998
- ◆ Developed to an academic software, ASITIC, which can simulate all kinds of passive elements.
- ◆ Conductors are assumed to be infinitely thin, *i.e.*, the thickness is ignored
- ◆ Direct extending to 3-D meets problems

[R. Gharpurey, *CICC'96*]

[A.M. Niknejad, *TCAD'98*]

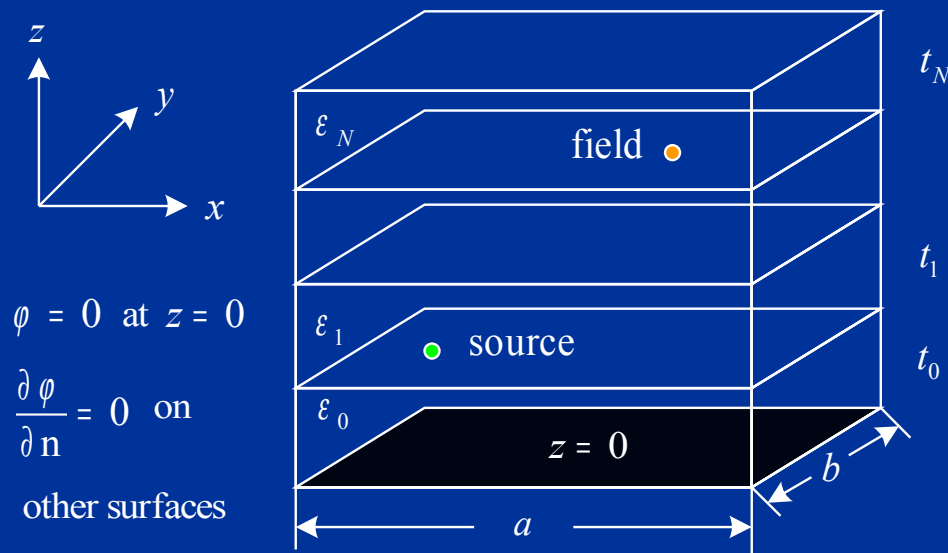
# Metal thickness

- ◆ Metal width and spacing are getting smaller and smaller, while the thickness is not reducing, sometimes even increases.
- ◆ Metal thickness should be considered.

# Boundary Conditions and Green's Function

$$\Delta G(r', r) = -\frac{\delta(r - r')}{\epsilon'}$$

$$\epsilon' = \epsilon + \frac{\sigma}{j\omega} \quad (\text{complex permittivity})$$



$$G = X(x', x)Y(y', y)Z(z', z)$$

$$X(x', x) = \cos\left(\frac{m\pi}{a} x'\right) \cos\left(\frac{m\pi}{a} x\right)$$

$$Y(x', x) = \cos\left(\frac{n\pi}{b} y'\right) \cos\left(\frac{n\pi}{b} y\right)$$

$Z(z', z)$  subjects to:

$$Z_k^l(z') = Z_k^u(z')$$

$$\frac{dZ_k}{dz} \Big|_{z'=+\delta_m} = -\frac{C_{mn}}{ab\epsilon_k}$$

$$Z_k|_{z=z_k} = Z_{k-1}|_{z=z_k}$$

$$\epsilon_k \frac{dZ_k}{dz} \Big|_{z=z_k} = \epsilon_{k-1} \frac{dZ_{k-1}}{dz} \Big|_{z=z_k}$$

$$Z_0|_{z=0} = 0$$

$$\frac{dZ_N}{dz} \Big|_{z=z_{N+1}} = 0$$



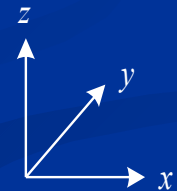
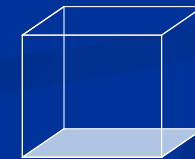
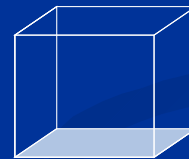
# Integration for the Coefficient of Potential

## ◆ Green's function

$$G = \sum_{m=0}^{\infty} \sum_{n=0}^{\infty} \cos(\delta_m x') \cos(\xi_n y') \cos(\delta_m x) \cos(\xi_n y) Z_{mn}(z', z)$$

$$p_{i,j} = \frac{1}{S_j S_i} \int_{S_i} \int_{S_j} G(x, x', y, y', z, z') ds_i ds_j$$

## ◆ For panels both on x-y plane

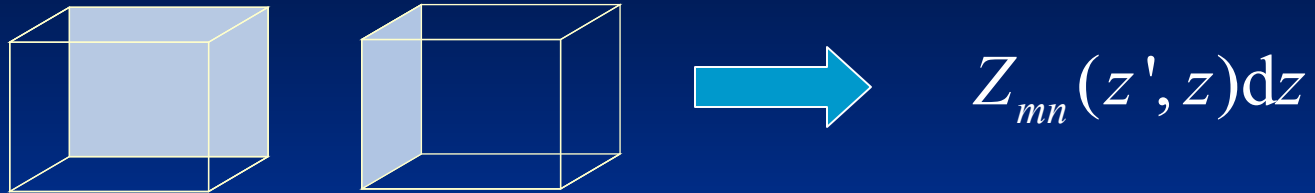


$$p_{ij} = \sum_{m,n} \int_{x_1}^{x_2} \int_{y_1}^{y_2} \cos(\delta_m x) \cos(\xi_n y) \cos(\delta_m x') \cos(\xi_n y') Z_{mn}(z', z) dx dy dx' dy'$$

64 terms

◆ **DCT** (Discrete Cosine Transform)

# For Sidewall Panels...



## ◆ Gharpurey'96 (original one)

$$Z_{mn}(z', z) = \frac{f_{mn}(z')}{\beta_s^u \Gamma_s^l - \beta_s^l \Gamma_s^u} \left[ \Gamma_f^{u,l} \cosh(\gamma_{mn} z) + \Gamma_f^{u,l} \sinh(\gamma_{mn} z) \right]$$

numerically instable when  $\gamma_{mn}$  grows

## ◆ Niknejad'98 (resolved the numerical stability)

$$Z_{mn}(z', z) = \frac{4F_k^l(z_f, z_s)}{ab\epsilon_k \gamma_{mn}} \frac{\cosh(\vartheta_f - \vartheta_j) \cosh(\vartheta_f - \vartheta_{k+1})}{\cosh(\vartheta_f - \vartheta_k)}$$

stable but cannot be integrated analytically

# Numerically Stable and Analytically Integrable Formula

replace the hyperbolic functions to exponential ones:

$$\cosh(x) = \frac{e^x + e^{-x}}{2}, \quad \sinh(x) = \frac{e^x - e^{-x}}{2},$$

$$Z_{mn}(z', z) = \frac{C_{mn}}{ab\epsilon_s \gamma_{mn}} \bar{j} \frac{\left( \alpha_s^{u,l} e^{\gamma_{mn} z'} + \beta_s^{u,l} e^{-\gamma_{mn} z'} \right) \left( \alpha_f^{u,l} e^{\gamma_{mn} z} + \beta_f^{u,l} e^{-\gamma_{mn} z} \right)}{\alpha_s^u \beta_s^l - \alpha_s^l \beta_s^u}$$

recursive procedure for the coefficients

$$\begin{matrix} \text{踐} \\ \text{銷} \\ \text{顏} \end{matrix} \alpha_k^l = \frac{1}{2} \begin{matrix} \text{鵠} \\ \text{鵠} \\ \text{鵠} \end{matrix} (1 + p_k) e^{\gamma_{mn} t_{k-1}} (1 - p_k) e^{-\gamma_{mn} t_{k-1}} \begin{matrix} \text{踐} \\ \text{銷} \\ \text{顏} \end{matrix} \alpha_{k-1}^l$$

$$\begin{matrix} \text{踐} \\ \text{銷} \\ \text{顏} \end{matrix} \beta_k^l = \frac{1}{2} \begin{matrix} \text{鵠} \\ \text{鵠} \\ \text{鵠} \end{matrix} (1 - p_k) e^{\gamma_{mn} t_{k-1}} (1 + p_k) e^{\gamma_{mn} t_{k-1}} \begin{matrix} \text{踐} \\ \text{銷} \\ \text{顏} \end{matrix} \beta_{k-1}^l$$

Integration

$$Z_{mn}(z', z) dz = \frac{X}{\gamma_{mn}} \bar{j} \left( \alpha_f^{u,l} e^{\gamma_{mn} z} - \beta_f^{u,l} e^{-\gamma_{mn} z} \right)$$

# Stability-Preserving Technique

## ◆ Instability:

$e^{\gamma_{mn} t_{k-1}}$  overflows when  $\gamma_{mn}$

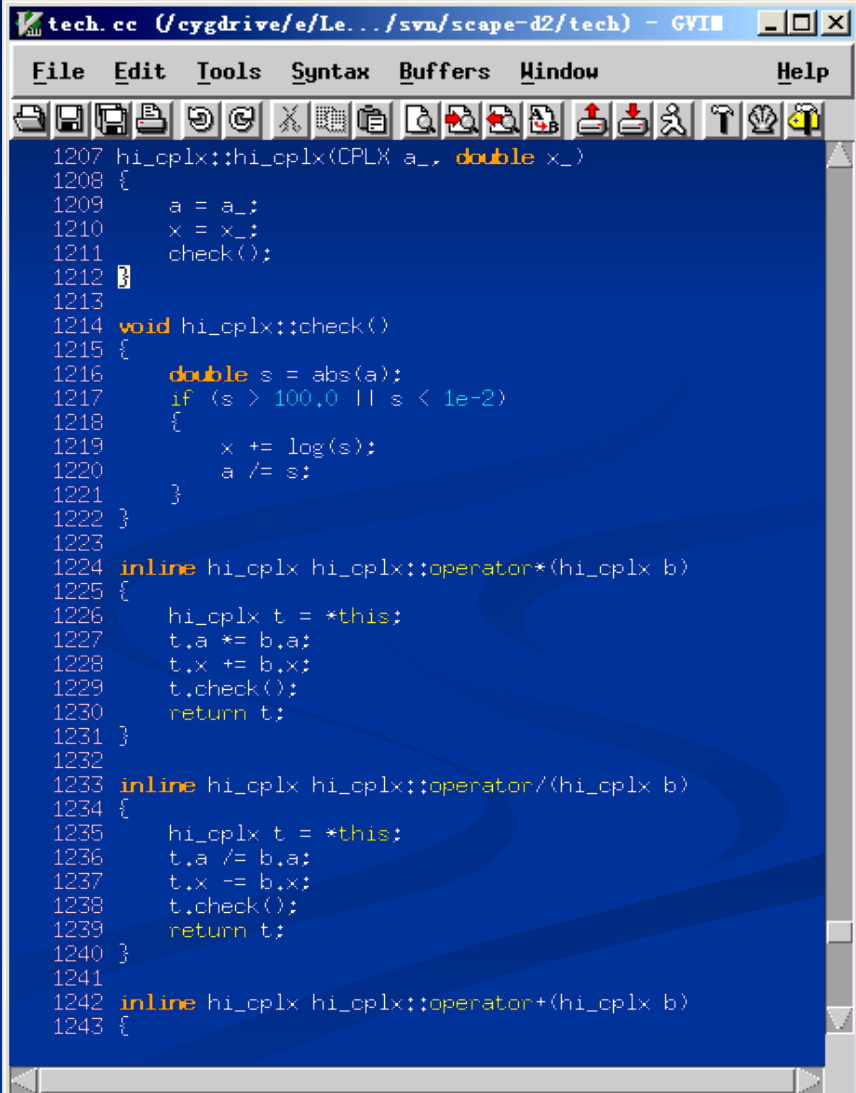
becomes large

## ◆ Solution:

- Define super complex number (hi\_cplx)

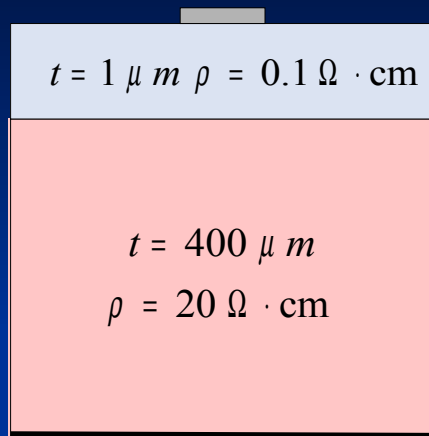
$$\text{hi\_cplx } z = ae^x \begin{matrix} a \dagger \mathbf{C} \\ x \dagger \mathbf{R} \end{matrix}$$

- Re-define (overload) the operators (+, -, \*, /) to avoid the overflow.

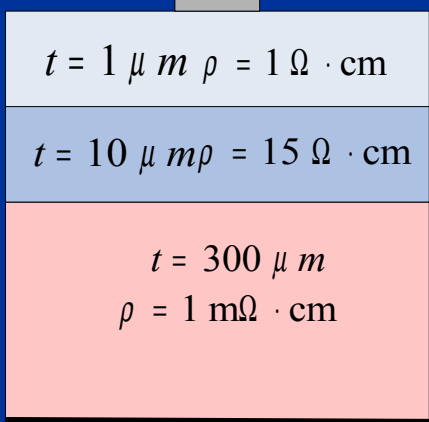


```
tech.cc (/cygdrive/e/Le.../svn/scape-d2/tech) - GVI
File Edit Tools Syntax Buffers Window Help
1207 hi_cplx::hi_cplx(CPLX a_, double x_)
1208 {
1209     a = a_;
1210     x = x_;
1211     check();
1212 }
1213
1214 void hi_cplx::check()
1215 {
1216     double s = abs(a);
1217     if (s > 100.0 || s < 1e-2)
1218     {
1219         x += log(s);
1220         a /= s;
1221     }
1222 }
1223
1224 inline hi_cplx hi_cplx::operator*(hi_cplx b)
1225 {
1226     hi_cplx t = *this;
1227     t.a *= b.a;
1228     t.x += b.x;
1229     t.check();
1230     return t;
1231 }
1232
1233 inline hi_cplx hi_cplx::operator/(hi_cplx b)
1234 {
1235     hi_cplx t = *this;
1236     t.a /= b.a;
1237     t.x -= b.x;
1238     t.check();
1239     return t;
1240 }
1241
1242 inline hi_cplx hi_cplx::operator+(hi_cplx b)
1243 {
```

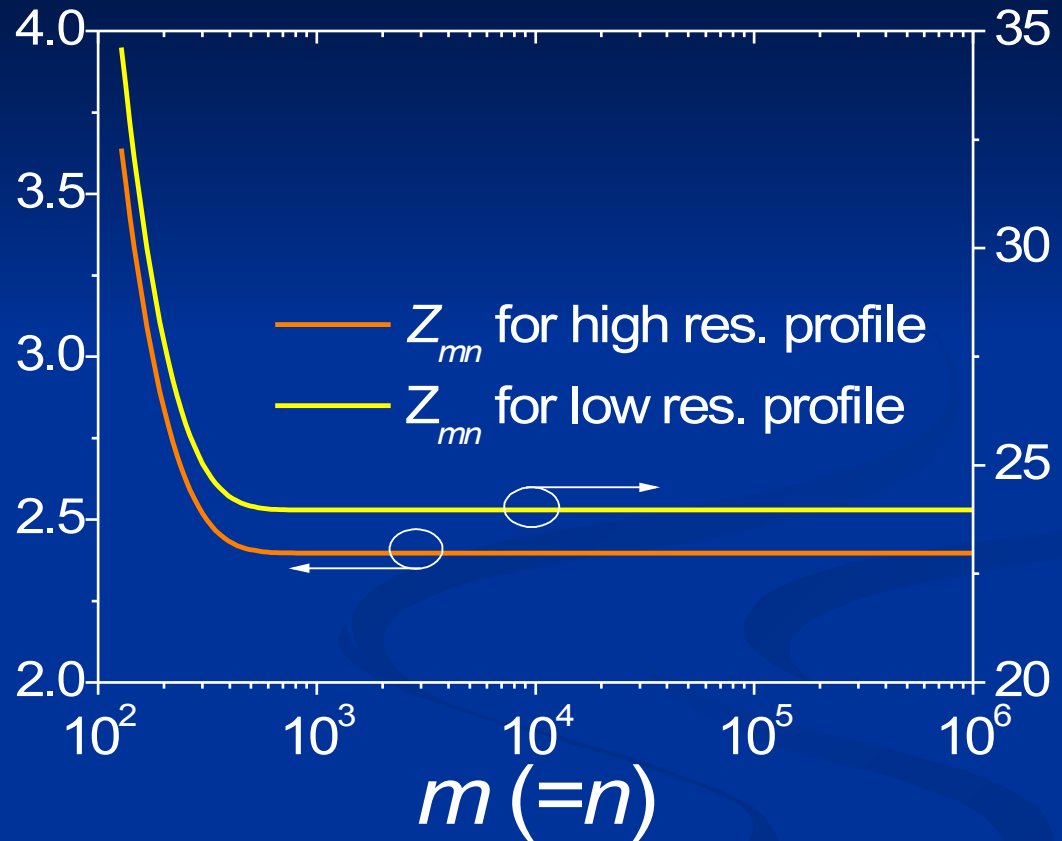
# Numerical Stability



High Resistivity



Low Resistivity

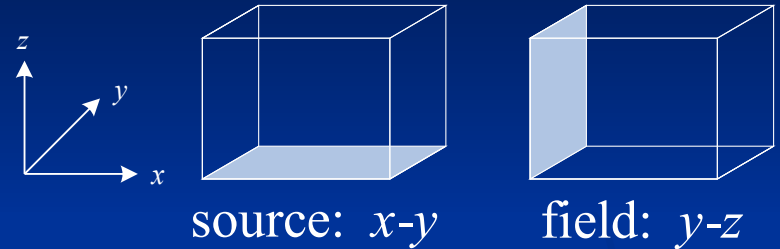


Stable even when  $m (=n)$  goes to extremely large (up to 1 million)

# Coefficient-of-Potential Involving Sidewalls: $xy$ - $yz$

$$p_{i,j} = \frac{1}{S_j S_i} \int_{S_i} \int_{S_j} G(x, x', y, y', z, z') ds_i ds_j$$

$$ds_i = dx dy \quad ds_j = dy dz$$



$$G = \sum_{m=0}^{\infty} \sum_{n=0}^{\infty} \underbrace{\cos(\delta_m x')}_{\sin} \underbrace{\cos(\delta_m x)}_{\cos} \underbrace{\cos(\xi_n y')}_{\sin} \underbrace{\cos(\xi_n y)}_{\sin} \underbrace{Z_{mn}(z', z)}_{Z_{mn}^{(1)}(z', z) (= \int Z_{mn} dz)}$$

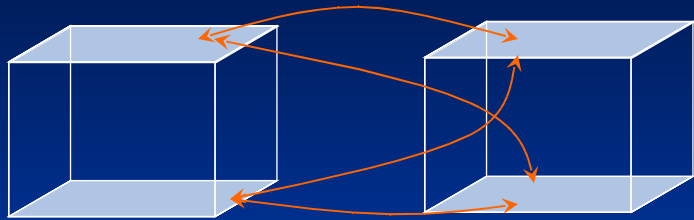
$$p_{ij} = \sum_{m,n} f_{mn}^{(1)}(z', z) \sin \frac{m\pi}{2} (x_{1,2} \uparrow x_3) \cos \frac{n\pi}{2} (y_{1,2} \uparrow y_{3,4})$$

32 terms

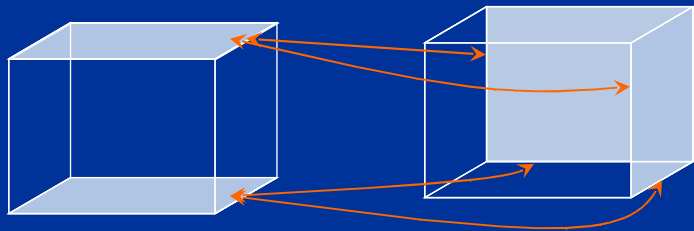
DCST (Discrete Cosine-Sine Transform)

# All Positional Relations

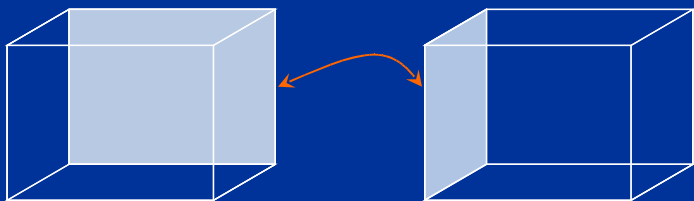
**DCT**



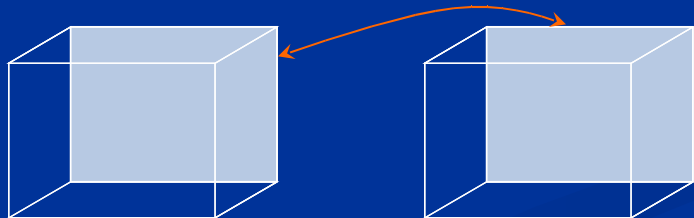
**DCST**



**DST**



**DCT**



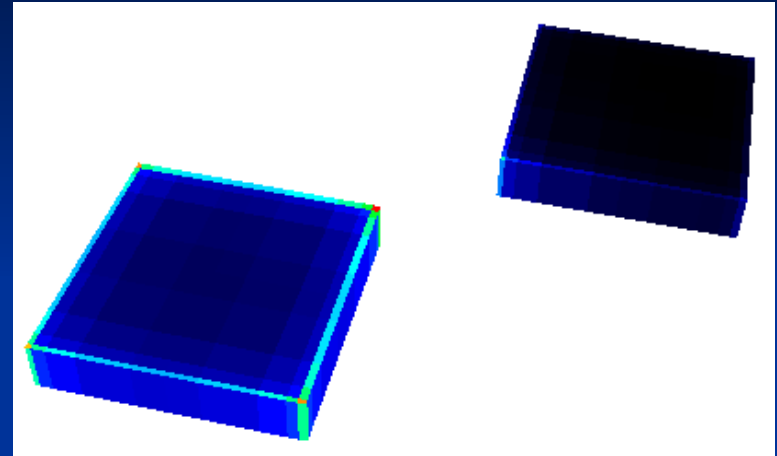
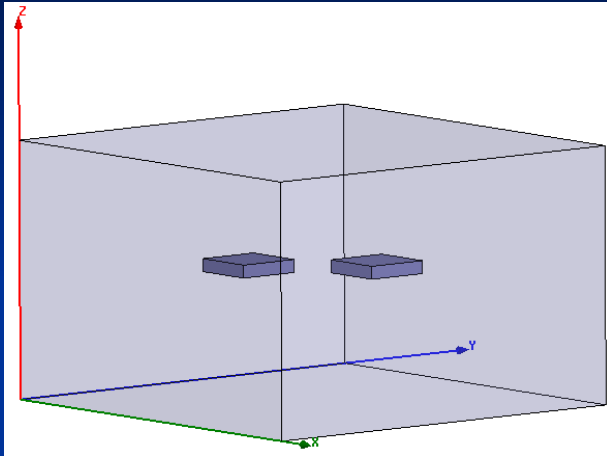
- ◆ Consider totally 10 situations classified to 4 types
- ◆ For each situation, a Green's function should be computed and stored
- ◆ It required about 10X of that cost by ASITIC
- ◆ Can be reduced by applying non-uniform grid

# Non-uniform Grid Method for Computing Green's Function

- ◆ FFT  $\longleftrightarrow$  uniform grid
  - Computational amount  $O(N^2 \log(N^2))$
  - Memory required:  $O(N^2)$  (N: FFT size,  $\sim 2000$ , increases with shrinking metal width)
- ◆ Non-uniform grid method have been developed (but not presented in the proceedings)
  - Computational amount  $O(M^2 N_c^2)$
  - Memory required:  $O(N_c^2)$
  - $N_c$ : non-uniform grid size,  $< 40$ ;  $M$ :  $\sim 64$  (constant)



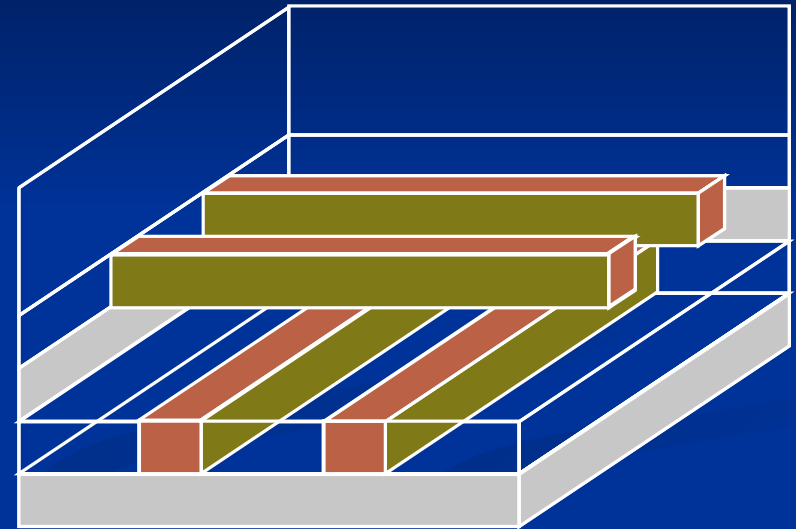
# Test Case I: Two contacts



	C11 (F)	Error (%)	C12 (F)	Error (%)
Ansys	6.2520e-15	--	-1.5668e-15	--
ASITIC	5.0121e-15	-19.8	-9.7422e-16	-37.8
SCAPE	6.2573e-15	-0.08	-1.5752e-15	0.54

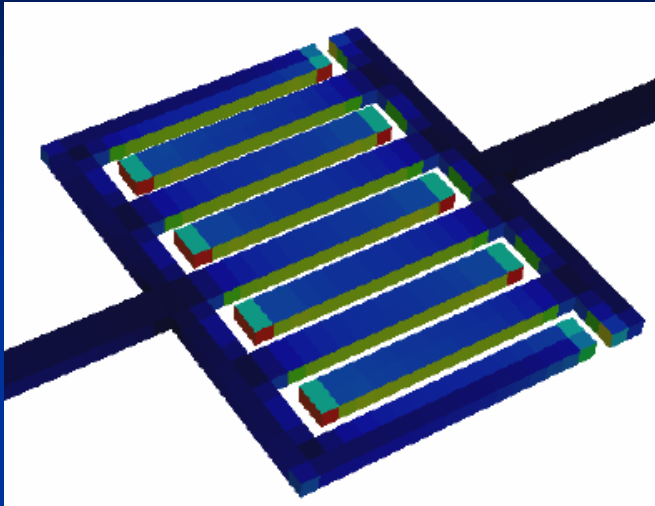
# Test Case II: $k$ -by- $k$ buses

	Test problem			
	2×2	3×3	4×4	5×5
FastCap I (with fine mesh)				
CPU Time (s)	54	120	218	349
Memory (MB)	111	131	160	197
Panel #	7812	8724	9948	11492
FastCap II (with coarse mesh)				
CPU Time (s)	11.6	19.1	31.1	46.6
Memory (MB)	56	64	75	89
Panel #	3628	4080	4684	5448
Error (%)	2.89	2.84	2.85	2.76
ASITIC				
Panel #	50	84	144	220
Error (%)	23.7	24.8	25.8	25.4
SCAPE				
CPU time (s)	0.32	1.14	3.41	8.39
Memory (MB)	19	20	21	25
Panel #	146	276	464	700
Error (%)	0.99	0.91	1.60	2.38



Green's function method does not need to discretize the interfaces of dielectrics

# Test case III: Interdigital Capacitor (IDC) over Lossy Substrate



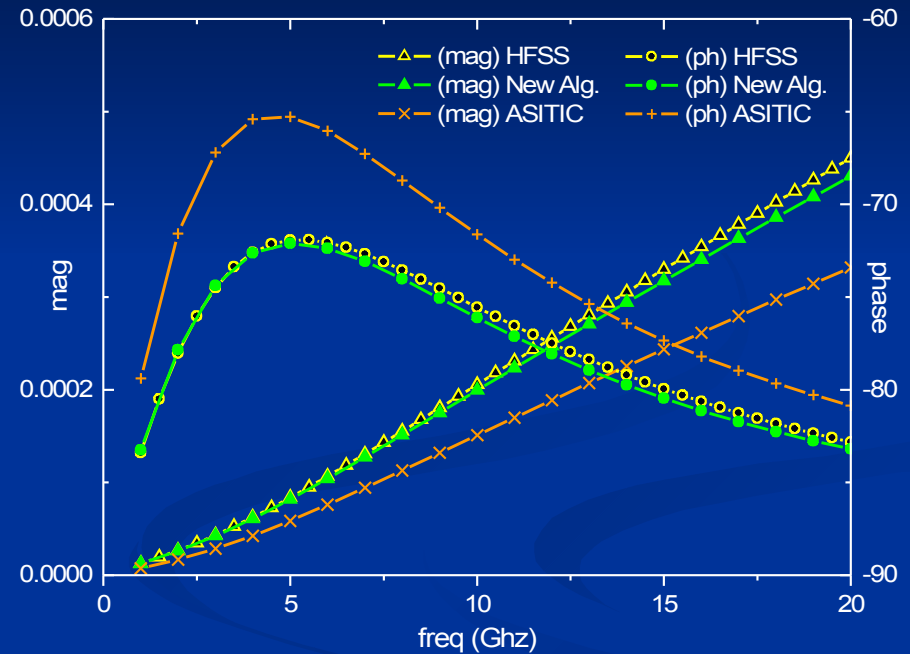
$$t_{metal} = 2 \mu m$$

$$\epsilon_{ox} = 3.9$$

$$t_{ox} = 1 \mu m$$

$$\epsilon_{sub} = 11.9$$

$$\rho_{sub} = 5 \Omega \cdot cm$$



Frequency dependence of the complex capacitance of the IDC.

# Conclusion

- ◆ 3-D capacitance extraction based on Green's function
- ◆ Stable and analytically integrable formula for the Green's function in z-direction
- ◆ Accurate result compared with well tested solvers (FastCap, Ansys, HFSS)
- ◆ Limitation: layered dielectric, Manhattan conductor

**Thank you**